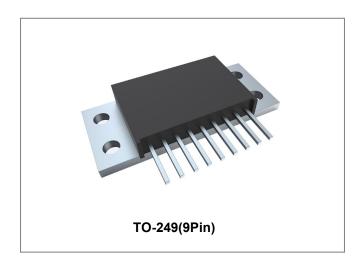






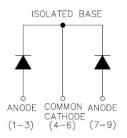
153CMQ080/153CMQ100 SCHOTTKY RECTIFIER



Features

- 175 °C T_J operation
- Isolated heatsink
- Multiple leads per terminal for high frequency, high current PC board mounting
- Low profile, high current package
- Center tap module
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Schematic & Pin Configuration



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.		Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage	$V_{RRM} \ V_{RWM}$		80	153CMQ080	V
DC Blocking Voltage	VRWM VR	-	100	153CMQ100	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @T _C =90°C, rectangular wave form	75(Per Leg) 150(Per Device)		Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	864		Α
Non-Repetitive Avalanche Energy (Peg Leg)	Eas	T _J =25℃,I _{AS} =1A,L=30mH	15		mJ
Repetitive Avalanche Current(Peg Leg)	I _{AR}	Current decaying linearly to zero in 1 µsec Frequency limited by T _J max. V _A =1.5×V _R typical		1	А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Peg Leg)*	V _{F1}	@ 75A, Pulse, T _J = 25 °C @ 150A, Pulse, T _J = 25 °C	0.80	0.96 1.19	V
	V _{F2}	@ 75A, Pulse, T _J = 125 °C @ 150A, Pulse, T _J = 125 °C	0.67 -	0.80 0.99	V
Reverse Current(Peg Leg)*	I _{R1}	@V _R = rated V _R ,T _J = 25 °C	0.005	1.5	mA
	I _{R2}	$@V_R = \text{rated } V_R, T_J = 125 ^{\circ}\text{C}$	20	50	mA
Junction Capacitance(Peg Leg)	Ст	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	1200	1400	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

^{*} Pulse width < 300 µs, duty cycle < 2%

Thermal-Mechanical Specifications:

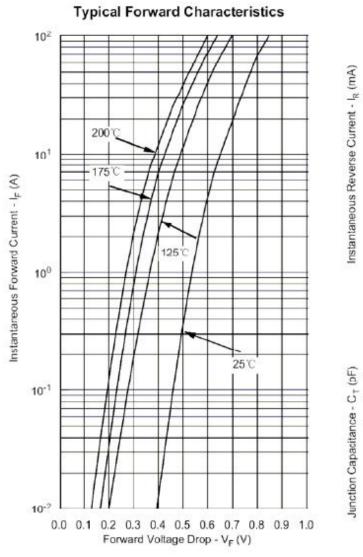
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case (Per Leg)	R _{θJC}	DC operation	1.0	°C/W
Typical Thermal Resistance Junction to Case (Per Package)	$R_{ heta JC}$	DC operation	0.50	°C/W
Typical Thermal Resistance, case to Heat Sink	R _{θcs}	Mounting surface, smooth and greased	0.10	°C/W
Mounting Torque	T _M	-	40(min)	Kg-cm
			58(max)	Ng-cill
Approximate Weight	wt	-	56	g
Case Style	TO-249(9 pin)			



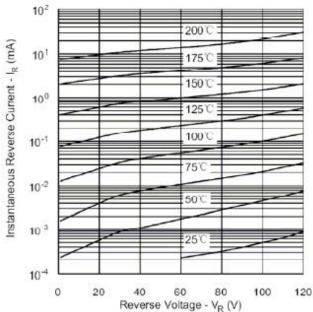




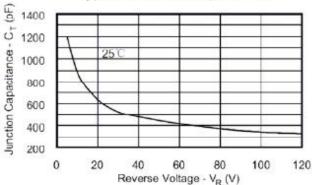
Ratings and Characteristics Curves



Typical Reverse Characteristics



Typical Junction Capacitance



Ordering Information

Device	Package	Shipping
153CMQ SERIES	TO-249(Pb-Free)	24pcs/ box

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

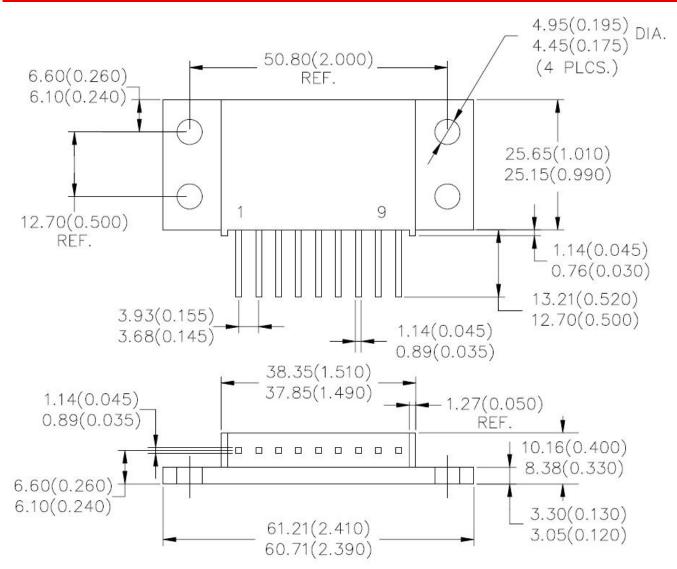
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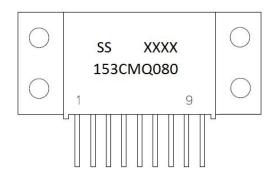




Mechanical Dimensions TO-249(9pin) (Inches/Millimeters)



Marking Diagram



Where XXXX is YYWW

1st row SS YYWW
2nd row 153CMQ080
3rd row 1 2 3 (pin)
SS = SS
YY = Year
WW = Week

Cautions: Molding resin

Epoxy resin UL:94V-0

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153CMQ...SERIES



Technical Data Data Sheet N1237, Rev. A





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